ABSTRACT

INTEGRATED CIRCUIT HAVING A PLURALITY OF MOSFET DEVICES

A method is provided for manufacturing an integrated circuit having a plurality of MOSFET devices, comprising the steps of: providing a plurality of MOSFET devices each having a first and a second structural parameter associated therewith, wherein a value of one of the first and a second structural parameter of each device is selected to provide a value of a performance parameter of the device substantially equal to a predetermined reference value, the predetermined reference value being the same for each device.

Fig 4